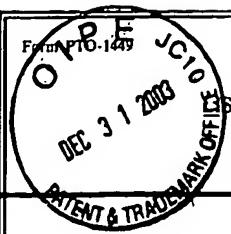


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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CDW	AA	6,593,624 B2	07/03	Walker	257	344	
CDW	AB	6,204,608 B1	03/01	Song et al.	315	169.3	
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FOREIGN PATENT DOCUMENTS

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	AO							
	AP							
	AQ							

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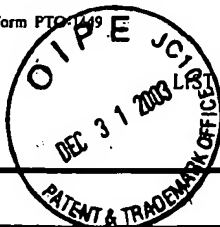
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U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CDW	AA	US 2003/ 0013305 A1	Pub. 01/03	Sugii et al.	438	689	06/07/02
CDW	AB	US 2002/ 0045312 A1	Pub. 04/02	Zheng et al.	438	253	07/19/01
CDW	AC	US 2002/ 0014625 A1	Pub. 02/02	Asami et al.	257	57	08/01/01
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FOREIGN PATENT DOCUMENTS

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya	
				PRIORITY FILING DATE September 12, 2002	GROUP 2824
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
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	AB		Yamauchi, N. et al., "Drastically Improved Performance in Poly-Si TFTs with Channel Dimensions Comparable to Grain Size", IEDM Tech. Digest, 1989, pp. 353-356.		
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	AD		Kuriyama, H. et al., "High Mobility Poly-Si TFT by a New Excimer Laser Annealing Method for Large Area Electronics", IEDM Tech. Digest, 1991, pp. 563-566.		
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	AL		Garone, P.M. et al., "Mobility Enhancement and Quantum Mechanical Modeling in $\text{Ge}_2\text{Si}_{1-x}$ Channel MOSFETs from 90 to 300K", IEDM Tech. Digest, 1991, pp. 28-32.		
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya			
				PRIORITY FILING DATE September 12, 2002		GROUP 2824	
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CW	AX	Mizuno, T. et al., "High Performance CMOS Operation of Strained-SOI MOSFETs Using Thin Film SiGe-on-Insulator Substrate", 2002 Sympos. on VLSI Tech. Digest of Technical Papers, p. 106-107.
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	BA	"IBM Builds World's Fastest Communications Microchip", Reuters U.S. Company News, 2/25/2002, reprinted from http://activequote300.fidelity.com/rtrnews/Individual_n.../... , 1 pg.
	BB	Markoff, J., "I.B.M. Circuits are Now Faster and Reduce Use of Power", The New York Times, Feb. 25, 2002, reprinted 3/20/02 from http://story.news.yahoo.com/news?tmpl=story&u=/nyt/20020225/... , 1 pg.
	BC	Park, J.S. et al., "Normal Incident SiGe/Si Multiple Quantum Well Infrared Detector", IEDM Tech. Digest, 1991, pp. 749-752.
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	BE	Bhattacharyya, A., "The Role of Microelectronic Integration in Environmental Control: A Perspective", Mat. Res. Soc. Symp. Proc. Vol. 344, 1994, pp. 281-293.
	BF	Myers, S.M. et al., "Deuterium Interactions in Oxygen-Implanted Copper", J. Appl. Phys., Vol. 65(1), Jan. 1, 1989, p. 311-321.
	BG	Saggio, M. et al., "Innovative Localized Lifetime Control in High-Speed IGBT's", IEEE Elec. Dev. Lett., V. 18, No. 7, July 1997, pp. 333-335.
	BH	Lu, N.C.C. et al., "A Buried-Trench DRAM Cell Using a Self-Aligned Epitaxy Over Trench Technology", IEDM Tech. Digest, 1988, pp. 588-591.
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Arup BhattacharyyaPRIORITY FILING DATE
September 12, 2002

GROUP 2824

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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		nm Applications", 2001 IEEE Intermat. SOI Conf. 10/01, pp. 45-46.
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